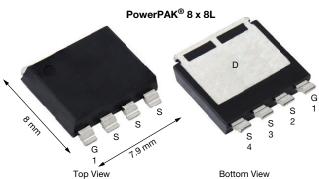


Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



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FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Thin 1.6 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

N-Channel MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0011
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.00080
I _D (A) ^e	461
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SQJQ160EL (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	60	V		
Gate-source voltage		V_{GS}	± 20	V		
Continuous drain current ^e	T _C = 25 °C	1-	461			
	T _C = 125 °C	I _D	266			
Continuous source current (diode conduction)		I _S	317	Α		
Pulsed drain current a, e		I _{DM}	655			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	69			
Single pulse avalanche energy	L = 0.1 IIII	E _{AS}	238	mJ		
Maximum power dissipation ^e	T _C = 25 °C	P _D	348	W		
	T _C = 125 °C		116	VV		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak temperature) ^c			260	C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	R_{thJA}	44	°C/W	
Junction-to-case (drain) ^d		R_{thJC}	0.43	C/VV	

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257)
- e. Values based on RthJC and TC of 25 °C- Actual values achievable will be dependent on the thermal characteristics of the complete system



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							,
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		1.5	2.0	2.5	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	μA
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	500	
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	50	-	-	Α
Drain-source on-state resistance ^a		$V_{GS} = 4.5 \text{ V}$	I _D = 20 A	-	0.00090	0.0011	
	_	V _{GS} = 10 V	I _D = 20 A	-	0.00056	0.00080	Ω
	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0014	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0017	
Forward transconductance b	9fs	V _{DS} = 15 V, I _D = 40 A		-	205	-	S
Dynamic ^b							
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	13 236	18 531	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	4447	6226	
Reverse transfer capacitance	C _{rss}			-	219	307	
Total gate charge ^c	Qg		V _{DS} = 30 V, I _D = 50 A	-	206	309	nC
Gate-source charge ^c	Q_{gs}	$V_{GS} = 10 \text{ V}$		-	42	-	
Gate-drain charge c	Q_{gd}			-	31	-	1
Gate resistance	Rg	f = 1 MHz		0.4	1.6	3.2	Ω
Turn-on delay time ^c	t _{d(on)}				17	26	
Rise time ^c	t _r	$V_{DD} = 30 \text{ V, } R_L = 0.6 \Omega,$ $I_D \cong 50 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	13	20	
Turn-off delay time ^c	t _{d(off)}			-	82	123	ns -
Fall time ^c	t _f			-	20	30	
Source-Drain Diode Ratings and Charac	teristics ^b						
Pulsed current ^a	I _{SM}			-	-	655	Α
Forward voltage	V_{SD}	$I_F = 40 \text{ A}, V_{GS} = 0 \text{ V}$		-	0.7	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		-	86	172	ns
Body diode reverse recovery charge	Q _{rr}			-	174	348	nC
Reverse recovery fall time	ta			-	50	-	
Reverse recovery rise time	t _b			-	37	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	3.5	-	Α
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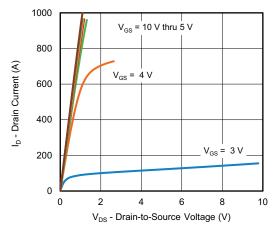
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

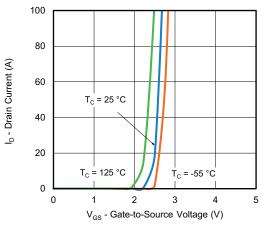
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



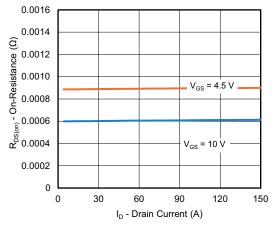
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



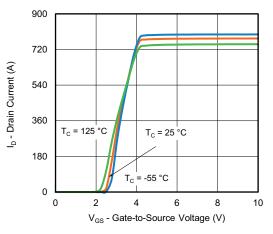
Output Characteristics



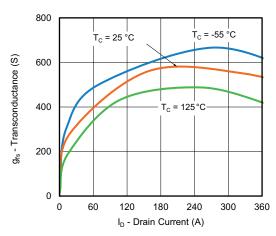
Transfer Characteristics



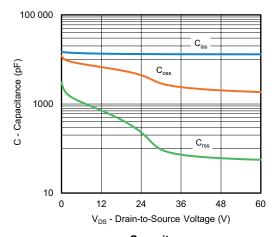
On-Resistance vs. Drain Current



Transfer Characteristics



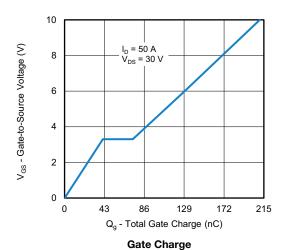
Transconductance

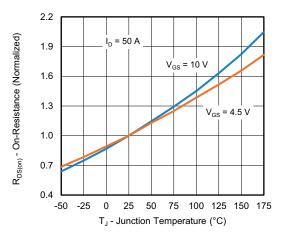


Capacitance

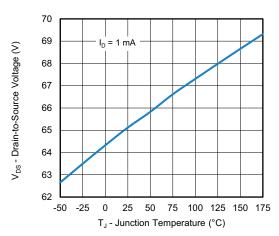


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

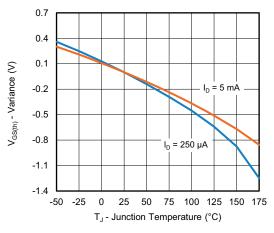




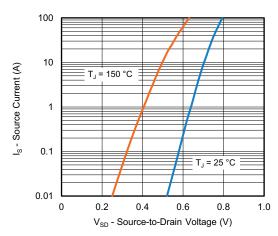
On-Resistance vs. Junction Temperature



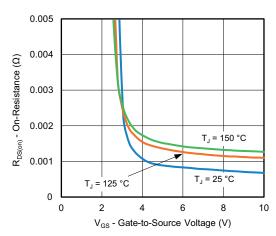
Drain Source Breakdown vs. Junction Temperature



Threshold Voltage



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

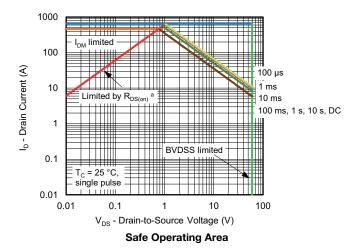
Note

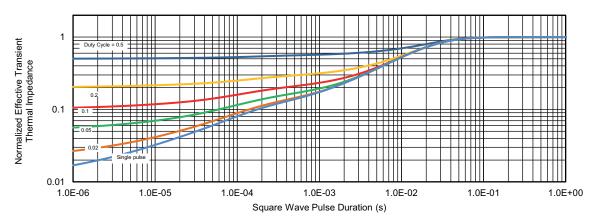
a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

For technical questions, contact: automostechsu

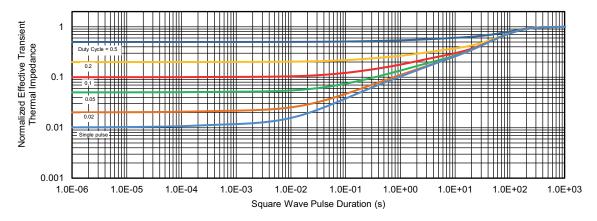


THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)





Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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